

MOSFET – Power, Single N-Channel 40 V, 378 A, 0.7 mΩ NVMFS5C4O4N

Features

- Small Footprint (5x6 mm) for Compact Design
- Low R_{DS(on)} to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- NVMFS5C404NWF Wettable Flank Option for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Symbol	Parar	Value	Unit		
V _{DSS}	Drain-to-Source Voltag	40	V		
V_{GS}	Gate-to-Source Voltage	±20	V		
I _D	Continuous Drain		T _C = 25°C	378	Α
	Current R _{0JC} (Notes 1, 3)	Steady	T _C = 100°C	267	
P _D	Power Dissipation	State	T _C = 25°C	200	W
	R _{θJC} (Note 1)		T _C = 100°C	100	
I _D	Continuous Drain		T _A = 25°C	53	Α
	Current R _{0JA} (Notes 1, 2, 3)	Steady	T _A = 100°C	37	
P_{D}	Power Dissipation	State	T _A = 25°C	3.9	W
	R _{θJA} (Notes 1, 2)		T _A = 100°C	1.9	
I _{DM}	Pulsed Drain Current	T _A = 25	°C, t _p = 10 μs	900	Α
T _J , T _{stg}	Operating Junction and Range	-55 to +175	°C		
I _S	Source Current (Body D	191	Α		
E _{AS}	Single Pulse Drain-to-S Energy (I _{L(pk)} = 38 A)	907	mJ		
T _L	Lead Temperature for S (1/8" from case for 10 s		urposes	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

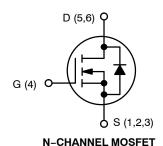
Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Junction-to-Case - Steady State	0.75	°C/W
$R_{\theta JA}$	Junction-to-Ambient - Steady State (Note 2)	39	

The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

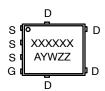
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.

V _{(BR)DSS}	R _{DS(ON)} MAX	I _D MAX
40 V	0.7 m Ω @ 10 V	378 A





MARKING DIAGRAMS



XXXXXX = Specific Device Code A = Assembly Location

Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 5.

Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Cond	Test Condition		Тур	Max	Unit
OFF CHAR	ACTERISTICS	•		•	•	•	•
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	V _{GS} = 0 V, I _D =	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$				٧
V _{(BR)DSS} / T _J	Drain-to-Source Breakdown Voltage Temperature Coefficient				19.7		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} = 0 V,	T _J = 25 °C			10	
		V _{DS} = 40 V	T _J = 125°C			250	μΑ
I_{GSS}	Gate-to-Source Leakage Current	$V_{DS} = 0 V, V_{GS}$	V _{DS} = 0 V, V _{GS} = 20 V			100	nA
ON CHARA	CTERISTICS (Note 4)						
V _{GS(TH)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D}$	= 250 μΑ	2.0		4.0	V
V _{GS(TH)} /T _J	Threshold Temperature Coefficient				-6.2		mV/°C
R _{DS(on)}	Drain-to-Source On Resistance	V _{GS} = 10 V	I _D = 50 A		0.57	0.7	mΩ
9 _{FS}	Forward Transconductance	V _{DS} =15 V, I _D	= 50 A		210		S
CHARGES,	CAPACITANCES & GATE RESISTANCE						
C _{ISS}	Input Capacitance				8400		
C _{OSS}	Output Capacitance	V _{GS} = 0 V, f = 1 MH	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 25 V		4600		pF
C _{RSS}	Reverse Transfer Capacitance				120		
Q _{G(TOT)}	Total Gate Charge	V _{GS} = 10 V, V _{DS} = 2	V _{GS} = 10 V, V _{DS} = 20 V; I _D = 50 A		128		
Q _{G(TH)}	Threshold Gate Charge		V _{GS} = 10 V, V _{DS} = 20 V; I _D = 50 A		22		nC
Q _{GS}	Gate-to-Source Charge	.,			35		
Q_{GD}	Gate-to-Drain Charge	$V_{GS} = 10 \text{ V}, V_{DS} = 2$			26		
V _{GP}	Plateau Voltage				4.3		V
SWITCHING	G CHARACTERISTICS (Note 5)						
t _{d(ON)}	Turn-On Delay Time				16		
t _r	Rise Time	V _{GS} = 10 V, V _D	s = 20 V.		113		1
t _{d(OFF)}	Turn-Off Delay Time	I _D = 50 A, R _G	= 2.5 Ω		77		ns
t _f	Fall Time				109		1
DRAIN-SO	URCE DIODE CHARACTERISTICS				•	•	•
V_{SD}	Forward Diode Voltage	V _{GS} = 0 V,	$T_J = 25^{\circ}C$		0.76	1.2	
		I _S = 50 A	T _J = 125°C		0.63		V
t _{RR}	Reverse Recovery Time		<u>.</u>		96		
t _a	Charge Time	V _{GS} = 0 V, dlS/dt	= 100 A/us.		49		ns
t _b	Discharge Time	I _S = 50 /			47		1
Q _{RR}	Reverse Recovery Charge				189		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 4. Pulse Test: pulse width \leq 300 μ s, duty cycle \leq 2%.

^{5.} Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

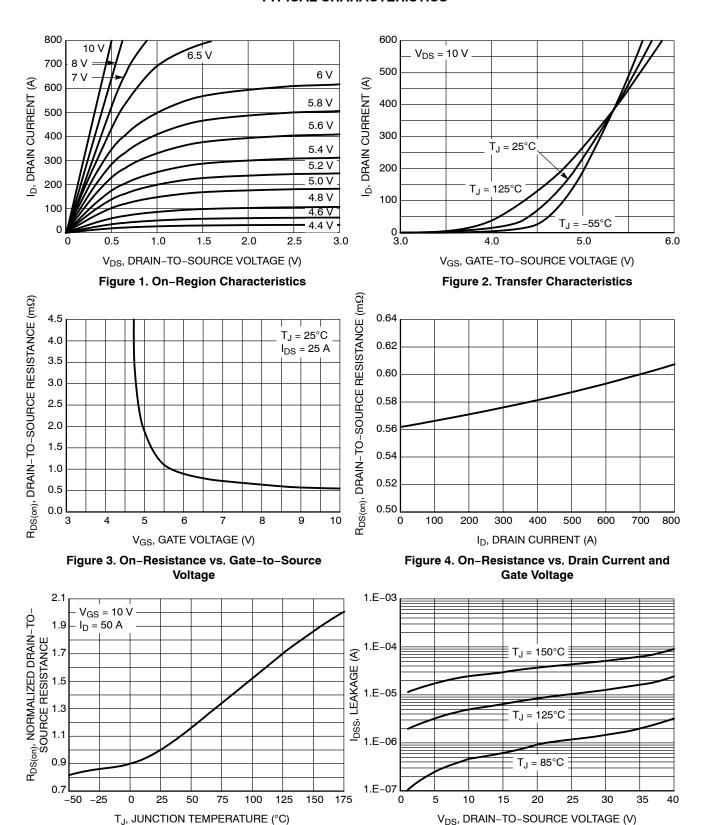


Figure 6. Drain-to-Source Leakage Current

vs. Voltage

Figure 5. On-Resistance Variation with

Temperature

TYPICAL CHARACTERISTICS

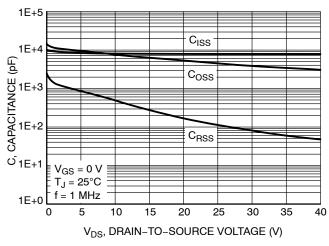


Figure 7. Capacitance Variation

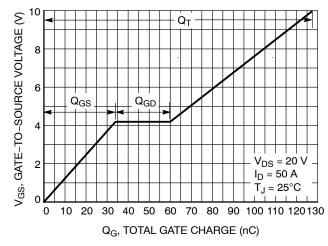


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

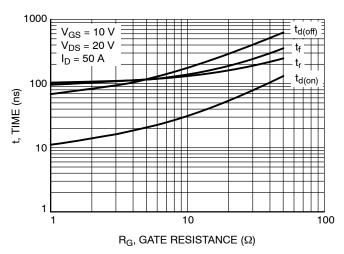


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

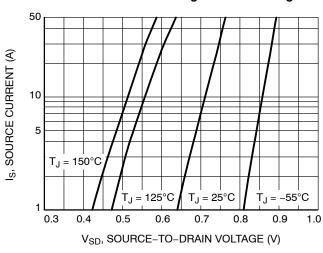


Figure 10. Diode Forward Voltage vs. Current

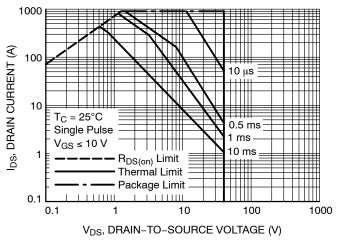


Figure 11. Maximum Rated Forward Biased Safe Operating Area

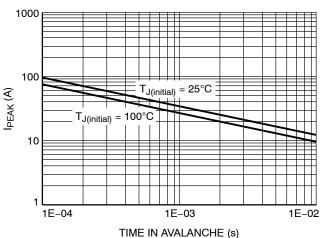


Figure 12. I_{PEAK} vs. Time in Avalanche

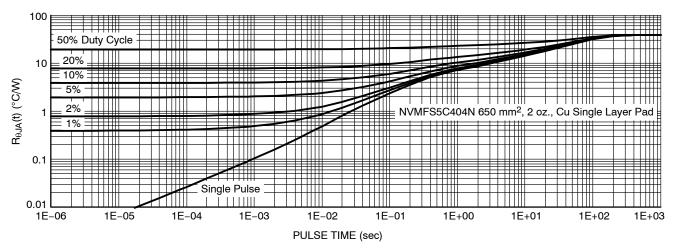


Figure 13. Thermal Characteristics

DEVICE ORDERING INFORMATION

Device	Case	Marking	Package	Shipping [†]
NVMFS5C404NT1G	506EZ	5C404N	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5C404NET1G	506EZ	5C404N	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5C404NAFT1G	506EZ	5C404N	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5C404NWFAFT1G	507BA	404NWF	DFNW5 (Pb-Free)	1500 / Tape & Reel
NVMFS5C404NWFET1G	507BA	404NWF	DFNW5 (Pb-Free)	1500 / Tape & Reel
NVMFS5C404NWFET3G	507BA	404NWF	DFNW5 (Pb-Free)	5000 / Tape & Reel

DISCONTINUED (Note 6)

NVMFS5C404NT3G	506EZ	5C404N	DFN5 (Pb-Free)	5000 / Tape & Reel
NVMFS5C404NWFT1G	507BA	404NWF	DFNW5 (Pb-Free)	1500 / Tape & Reel
NVMFS5C404NWFT3G	507BA	404NWF	DFNW5 (Pb-Free)	5000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{6.} **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

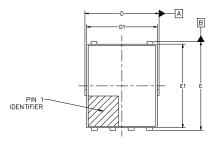




DFN5. 4.90 x 5.90 x 1.00. 1.27P CASE 506EZ **ISSUE B**

DATE 16 SEP 2024

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



TOP VIEW

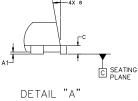
DETAIL "A"

SIDE VIEW

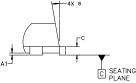
// 0.10 C

△ 0.10 C

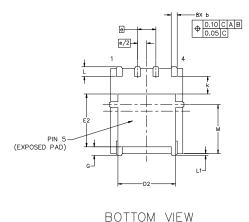




SCALED 2:1



MILLIMETERS						
DIM	MIN	NOM	MAX			
Α	0.90	1.00	1.10			
Α1	0.00		0.05			
b	0.33	0.41	0.51			
С	0.23	0.28	0.33			
D	5.00	5.15	5.30			
D1	4.70	4.90	5.10			
D2	3.80	4.00	4.20			
Е	6.00	6.15	6.30			
E1	5.70	5.90	6.10			
E2	3.45	3.80	3.85			
е	1	.27 BSC				
G	0.51	0.575	0.71			
k	1.10	1.20	1.40			
L	0.51	0.575	0.71			
L1	0	.125 RE	F			
М	3.00	3.40	3.80			
Θ	0.		12°			



GENERIC MARKING DIAGRAM*

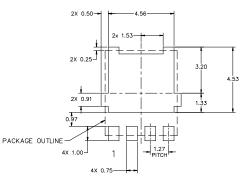


4	XXXXXX AYWZZ	
q		p

XXXXXX = Specific Device Code = Assembly Location Α

Υ = Year W = Work Week ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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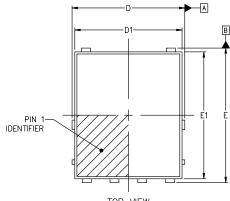
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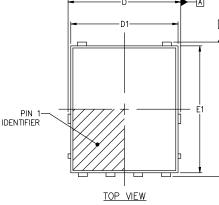


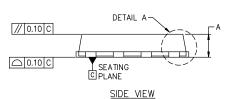


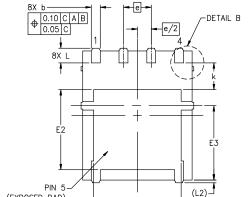
DFNW5 4.90x5.90x1.00, 1.27P CASE 507BA **ISSUE C**

DATE 19 SEP 2024





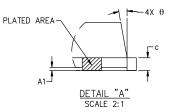


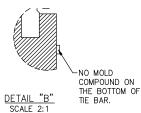


BOTTOM VIEW

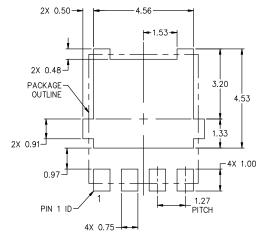
NOTES:

- DIMENSIONING TOLERANCING TO ASME Y14.5M-2018.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
- THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.





	VILLIMETERS	5
MIN	МОМ	MAX
0.90	1.00	1.10
0.00		0.05
0.33	0.41	0.51
0.23	0.28	0.33
5.00	5.15	5.30
4.70	4.90	5.10
3.80	4.00	4.20
6.00	6.15	6.30
5.70	5.90	6.10
3.45	3.65	3.85
3.00	3.40	3.80
	1.27 BSC	
1.20	1.35	1.50
0.51	0.57	0.71
	0.15 REF.	
0.	6*	12*
	MIN 0.90 0.00 0.33 0.23 5.00 4.70 3.80 6.00 5.70 3.45 3.00 0.51	MIN NOM 0.90 1.00 0.00 0.33 0.41 0.23 0.28 5.00 5.15 4.70 4.90 3.80 4.00 6.00 6.15 5.70 5.90 3.45 3.65 3.00 3.40 1.27 BSC 1.20 1.35 0.51 0.57 0.15 REF.



RECOMMENDED MOUNTING FOOTPRINT* *FOR ADDITIONAL INFORMATION ON OUR PD-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*

(EXPOSED PAD)



XXXXXX = Specific Device Code

= Assembly Location Α Υ = Year

W = Work Week ZZ = Lot Traceability *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

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